

Impinging Step Trains on a SiC Growth Surface



An interference contrast micrograph of a SiC growth surface. The 6H SiC crystal was grown by the seeded sublimation method at 2300 °C. The micrograph illustrates the point at which trains of growth steps from nearby sources (super screw dislocations) impinge. The steps originating from the lower right are almost ideal concentric circles. The steps progressing from the upper left exhibit instabilities, possibly caused by pinning points or competitive sources.

100 μm

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